

DESCRIPTION

2SC908 is a silicon NPN epitaxial planar type transistor designed for industrial use RF power amplifiers on UHF band mobile radio applications.

FEATURES

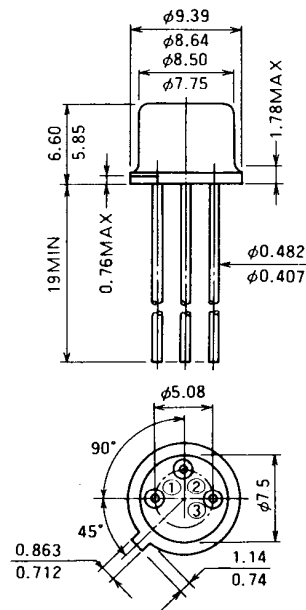
- High power gain: $G_{pe} \geq 4\text{dB}$
@ $V_{CC} = 13.5\text{V}$, $P_O = 1\text{W}$, $f = 500\text{MHz}$
- TO-39 metal sealed package for high reliability.
- All electrodes are isolated from the case.

APPLICATION

0.5 to 0.8 watt power amplifiers, and driver stage in UHF band.

OUTLINE DRAWING

Dimensions in mm



PIN :

- ① EMITTER
- ② BASE
- ③ COLLECTOR

T-8

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CBO}	Collector to base voltage		40	V
V_{EBO}	Emitter to base voltage		4	V
V_{CER}	Collector to emitter voltage	$R_{BE} = 10 \Omega$	40	V
I_C	Collector current		0.5	A
P_C	Collector dissipation	$T_a = 25^\circ\text{C}$	0.86	W
		$T_C = 25^\circ\text{C}$	4.3	W
T_j	Junction temperature		175	$^\circ\text{C}$
T_{stg}	Storage temperature		-65 to 175	$^\circ\text{C}$
R_{th-a}	Thermal resistance	Junction to ambient	175	$^\circ\text{C/W}$
R_{th-c}		Junction to case	35	$^\circ\text{C/W}$

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

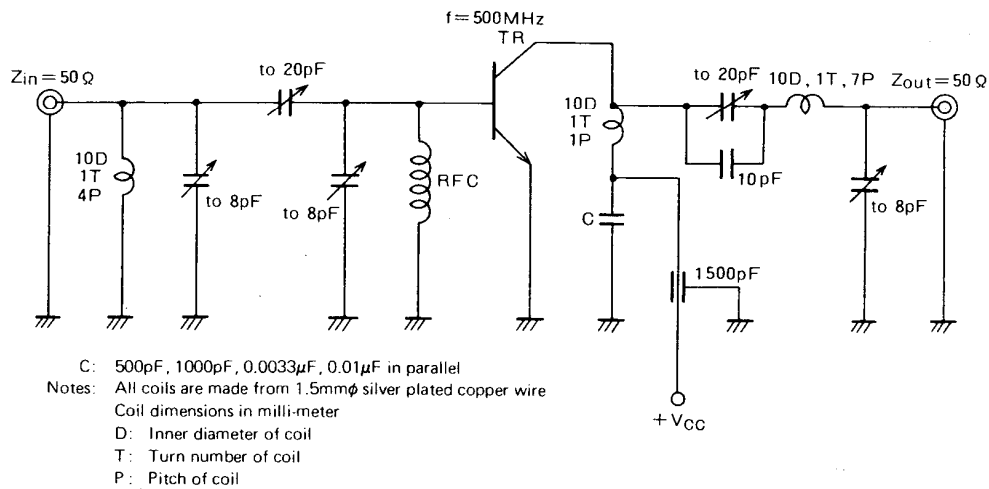
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 1\text{mA}$, $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$, $I_E = 0$	40			V
$V_{(BR)CER}$	Collector to emitter breakdown voltage	$I_C = 10\text{mA}$, $R_{BE} = 10 \Omega$	40			V
I_{CBO}	Collector cutoff current	$V_{CB} = 15\text{V}$, $I_E = 0$			50	μA
I_{EBO}	Emitter cutoff current	$V_{EB} = 3\text{V}$, $I_C = 0$			100	μA
h_{FE}	DC forward current gain *	$V_{CE} = 10\text{V}$, $I_C = 0.1\text{A}$	10	50	180	—
P_O	Output power	$V_{CC} = 13.5\text{V}$, $P_{in} = 0.4\text{W}$, $f = 500\text{MHz}$	1	1.2		W
η_C	Collector efficiency		50	70		%

Note. * Pulse test, $P_W = 150\mu\text{s}$, duty = 5%.

Above parameters, ratings, limits and conditions are subject to change.

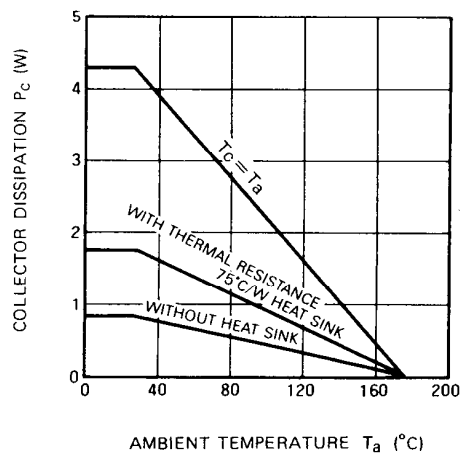
NPN EPITAXIAL PLANAR TYPE

TEST CIRCUIT

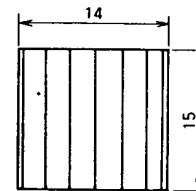
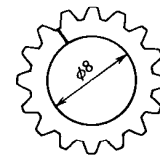


TYPICAL PERFORMANCE DATA

COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE

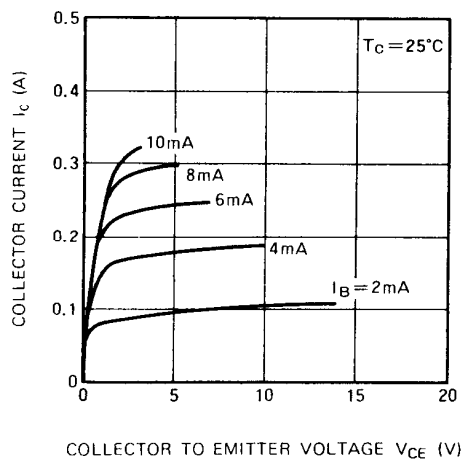


THERMAL RESISTANCE 75 $^{\circ}\text{C}$ HEAT SINK DRAWING

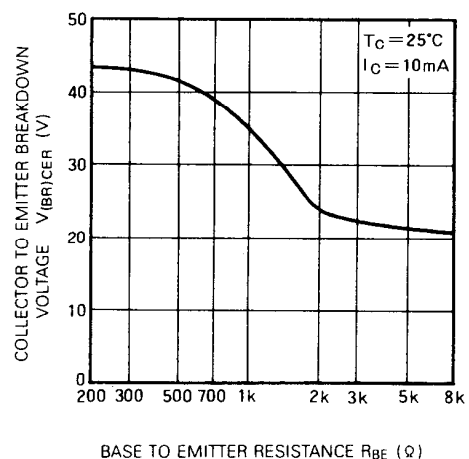


MATERIAL: Al
DIMENSIONS: mm

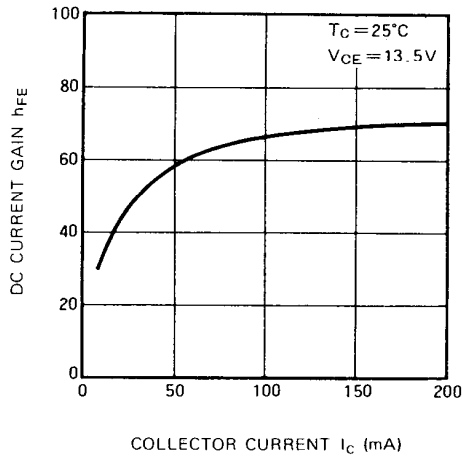
COLLECTOR CURRENT VS. COLLECTOR TO EMITTER VOLTAGE



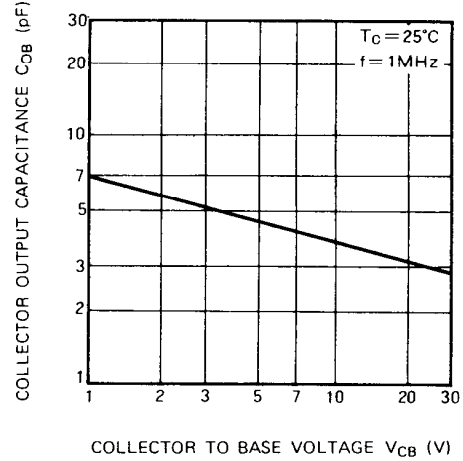
COLLECTOR TO EMITTER BREAKDOWN VOLTAGE VS. BASE TO EMITTER RESISTANCE



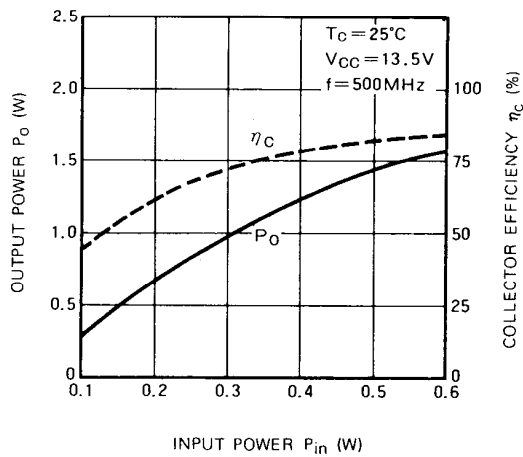
**DC CURRENT GAIN VS.
COLLECTOR CURRENT**



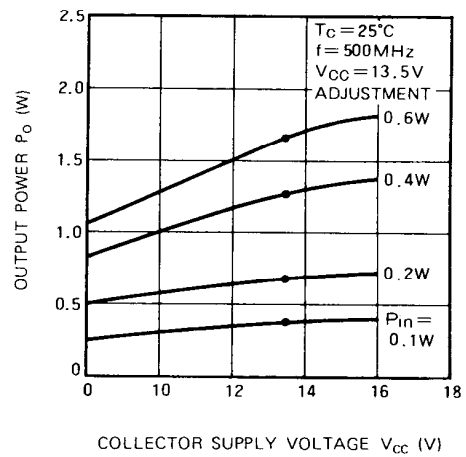
**COLLECTOR OUTPUT CAPACITANCE VS.
COLLECTOR TO BASE VOLTAGE**



**OUTPUT POWER VS. COLLECTOR
SUPPLY VOLTAGE**



**OUTPUT POWER,
COLLECTOR EFFICIENCY
VS. INPUT POWER**



**OUTPUT POWER VS.
FREQUENCY**

